

SILICON PRESS-FIT DIODES

VOLTAGE RANGE: 50 -- 600 V

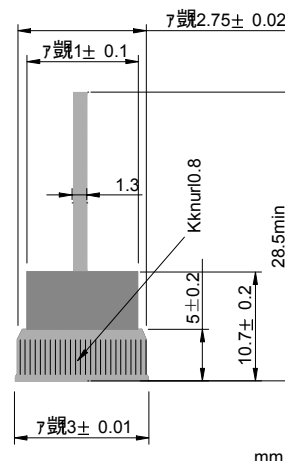
CURRENT: 35 A

FEATURES

- ◇ Nominal current 35A
- ◇ Repetitive peak reverse voltage 600 V
- ◇ Metal press-fit case with plastic cover
- ◇ Casting compound has UL classification

94V-0

BYP



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

Wire to anode		BYP 35A05	BYP 35A1	BYP 35A2	BYP 35A3	BYP 35A4	BYP 35A6	UNITS
Wire to cathode		BYP 35K05	BYP 35K1	BYP 35K2	BYP 35K3	BYP 35K4	BYP 35K6	
Repetitive peak reverse voltage	V _{RRM}	50	100	200	300	400	600	V
Surge peak reverse voltage	V _{RSM}	60	120	240	360	480	700	V
Max.average forward rectified current, R-load @T _C =150°C	I _{F(AV)}	35						A
Repetitive peak forward current f>15Hz (NOTE1)	I _{FRM}	110						A
Peak forward surge current,50/60 Hz half sine-wave	I _{FSM}	360/400						A
Forward voltage @ I _F =35A	V _F	1.1						V
Leakage current @T _j =25°C	I _R	100						A
Rating for fusing t<10ms	i ² t	A 660.0						² S
Thermal resistance junction to case	R _{thc}	0.8						K/W
Operating junction temperature	T _j	- 55 --- + 215						°C
Storage temperature range	T _S	- 55 --- + 215						°C

NOTE: Max.case temperature $T_C=150^{\circ}\text{C}$ -Max.

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FIG.1 – TYPICAL FORWARD CHARACTERISTIC

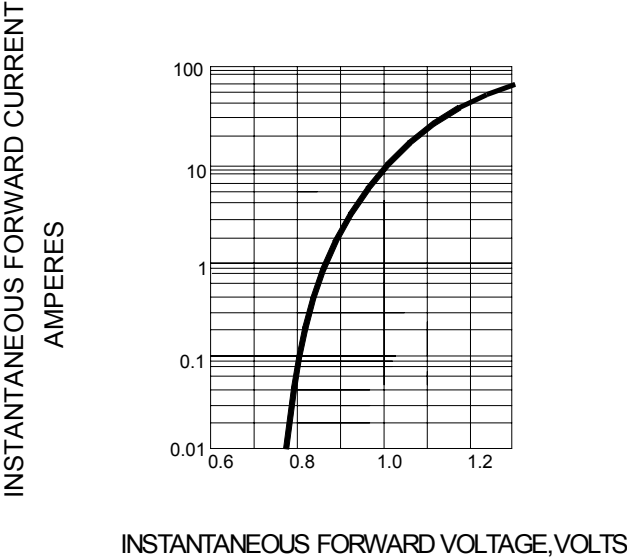


FIG.2 – FORWARD DERATING CURRENT

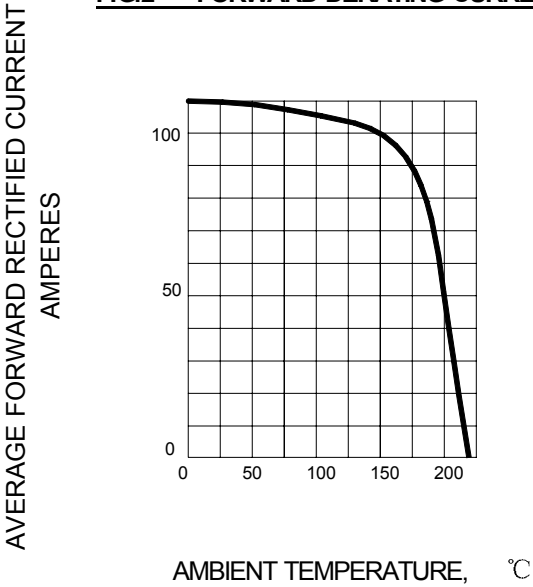


FIG.3 – PEAK FORWARD SURGE CURRENT

